

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-3. (Canceled)
4. (Currently Amended) An underlayer coating forming composition for forming a porous underlayer coating occupied by pores of 5 to 80% at a rate of volume for use in the manufacture of a semiconductor device, comprising a blowing agent, an organic material and a solvent, wherein a proportion of the blowing agent in solid content of the composition is 2 to 30 mass%, and wherein the blowing agent is selected from the group consisting of 4,4-oxybisbenzene sulfonyl hydrazide and azodicarbonamide.
- 5-6. (Canceled)
7. (Original) The underlayer coating forming composition according to claim 4, wherein the blowing agent is a blowing agent that is decomposed with heat to generate nitrogen, carbon dioxide or water vapor.
8. (Canceled)
9. (Previously Presented) The underlayer coating forming composition according to claim 4, wherein the organic material is an organic material containing at least one component selected from the group consisting of a polymer, a crosslinking compound and a light absorbing compound.
10. (Original) The underlayer coating forming composition according to claim 9, wherein the polymer is a polymer having at least one aromatic ring structure selected from the group consisting of a benzene ring, a naphthalene ring, an anthracene ring and a triazine ring.
11. (Original) The underlayer coating forming composition according to claim 9, wherein the crosslinking compound is a compound having at least two crosslink forming substituents.

12. (Original) The underlayer coating forming composition according to claim 9, wherein the light absorbing compound is a compound having at least one ring structure selected from the group consisting of a benzene ring, a naphthalene ring, an anthracene ring and a triazine trione ring.

13. (Previously Presented) A method for forming a photoresist pattern for use in the manufacture of a semiconductor device, comprising:

forming a porous underlayer coating occupied by pores of 5 to 80% at a rate of volume by applying the underlayer coating forming composition according to claim 4 on a semiconductor substrate and heating it;

forming a photoresist layer on the porous underlayer coating;

exposing the semiconductor substrate covered with the porous underlayer coating and the photoresist to light;

developing the photoresist after the exposure to light; and

removing the porous underlayer coating corresponding to a part of developed and removed photoresist by etching.